

PSMN7R0-30MLC

N-channel 30 V 7 mΩ logic level MOSFET in LFPAK33 using **NextPower Technology**

Rev. 4 — 15 June 2012

Product data sheet

Product profile 1.

1.1 General description

Logic level enhancement mode N-channel MOSFET in LFPAK33 package. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- Low parasitic inductance and resistance
- Optimised for 4.5V Gate drive utilising NextPower Superjunction technology

1.3 Applications

- DC-to-DC converters
- Load switching

1.4 Quick reference data

| Ultra low QG, QGD, & QOSS | for high |
|--------------------------------------|----------|
| system efficiencies at low and loads | l high |

Synchronous buck regulator

| Table 1. | Quick reference data | | | | | |
|---------------------|----------------------------------|---|-----|------|-----|------|
| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
| V _{DS} | drain-source voltage | T _j = 25 °C | - | - | 30 | V |
| I _D | drain current | T_{mb} = 25 °C; V_{GS} = 10 V; see <u>Figure 1</u> | - | - | 67 | А |
| P _{tot} | total power dissipation | T _{mb} = 25 °C; see <u>Figure 2</u> | - | - | 57 | W |
| Tj | junction temperature | | -55 | - | 175 | °C |
| Static cha | aracteristics | | | | | |
| R _{DSon} | drain-source on-state resistance | V _{GS} = 4.5 V; I _D = 15 A; T _j = 25 °C; see <u>Figure 10</u> | - | 7.8 | 9 | mΩ |
| | | V_{GS} = 10 V; I_D = 15 A; T_j = 25 °C; see <u>Figure 10</u> | - | 6.05 | 7 | mΩ |
| Dynamic | characteristics | | | | | |
| Q _{GD} | gate-drain charge | V_{GS} = 4.5 V; I_D = 15 A; V_{DS} = 15 V; see <u>Figure 12</u> ; see <u>Figure 13</u> | - | 2 | - | nC |
| Q _{G(tot)} | total gate charge | V_{GS} = 4.5 V; I_D = 15 A; V_{DS} = 15 V; see <u>Figure 12</u> ; see <u>Figure 13</u> | - | 8.2 | - | nC |



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2. Pinning information

| Table 2. | Pinning | information | | |
|----------|---------|-----------------------------------|--------------------|----------------|
| Pin | Symbol | Description | Simplified outline | Graphic symbol |
| 1 | S | source | | 2 |
| 2 | S | source | | D |
| 3 | S | source | | |
| 4 | G | gate | | |
| mb | D | mounting base; connected to drain | | mbb076 S |
| | | | SOT1210 (LFPAK33) | |

3. Ordering information

| Table 3. Ordering information | | | | | |
|---------------------------------------|---------|--|---------|--|--|
| Type number | Package | | | | |
| | Name | Description | Version | | |
| PSMN7R0-30MLC | LFPAK33 | Plastic single ended surface mounted package (LFPAK33); 4 leads | SOT1210 | | |

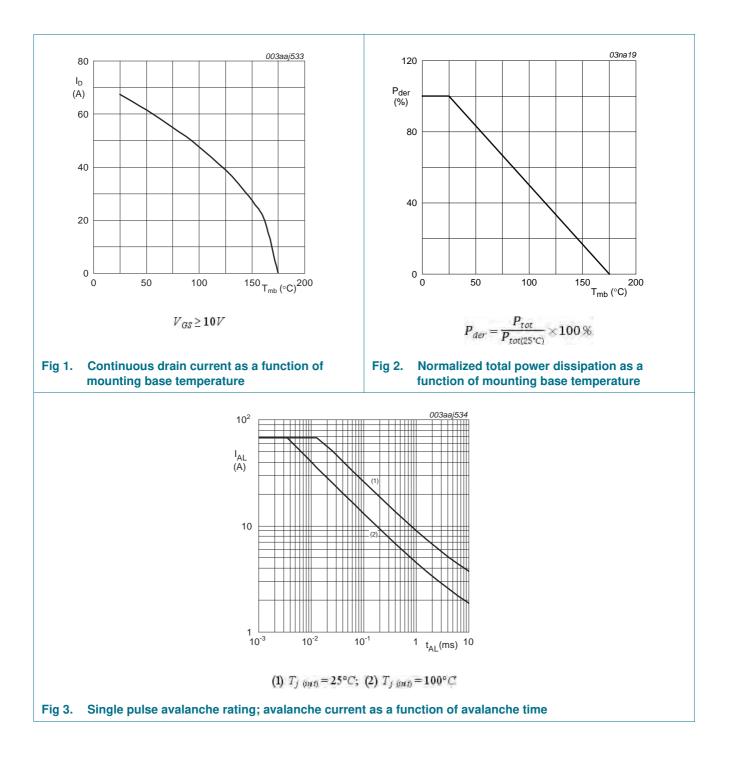
4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

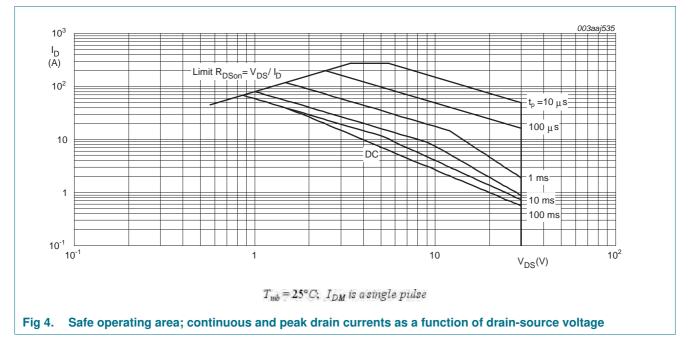
| Symbol | Parameter | Conditions | Min | Max | Unit |
|----------------------|---|---|-----|------|------|
| V _{DS} | drain-source voltage | $T_j = 25 \ ^{\circ}C$ | - | 30 | V |
| V _{GS} | gate-source voltage | | -20 | 20 | V |
| I _D | drain current | V_{GS} = 10 V; T_{mb} = 25 °C; see <u>Figure 1</u> | - | 67 | А |
| | | V_{GS} = 10 V; T_{mb} = 100 °C; see <u>Figure 1</u> | - | 48 | А |
| I _{DM} | peak drain current | pulsed; t _p ≤ 10 μs; T _{mb} = 25 °C; see <u>Figure 4</u> | - | 270 | A |
| P _{tot} | total power dissipation | T _{mb} = 25 °C; see <u>Figure 2</u> | - | 57 | W |
| T _{stg} | storage temperature | | -55 | 175 | °C |
| Tj | junction temperature | | -55 | 175 | °C |
| T _{sld(M)} | peak soldering temperature | | - | 260 | °C |
| V _{ESD} | electrostatic discharge voltage | MM (JEDEC JESD22-A115) | 190 | - | V |
| Source-drain | diode | | | | |
| I _S | source current | T _{mb} = 25 °C | - | 52 | А |
| I _{SM} | peak source current | pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$ | - | 270 | Α |
| Avalanche ru | ggedness | | | | |
| E _{DS(AL)S} | non-repetitive drain-source avalanche energy | $ \begin{array}{l} V_{GS} = 10 \; V; \; T_{j(init)} = 25 \; ^{\circ}C; \; I_{D} = 67 \; A; \\ V_{sup} \leq 30 \; V; \; R_{GS} = 50 \; \Omega; \; unclamped; \\ see \; \underline{Figure \; 3} \end{array} $ | - | 18.7 | mJ |

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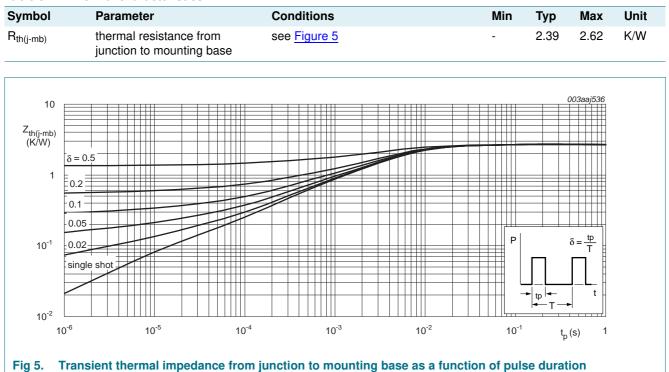
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5. Thermal characteristics

Table 5. Thermal characteristics



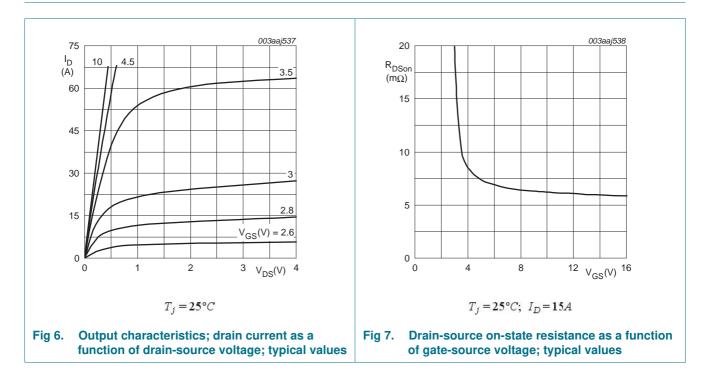
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6. Characteristics

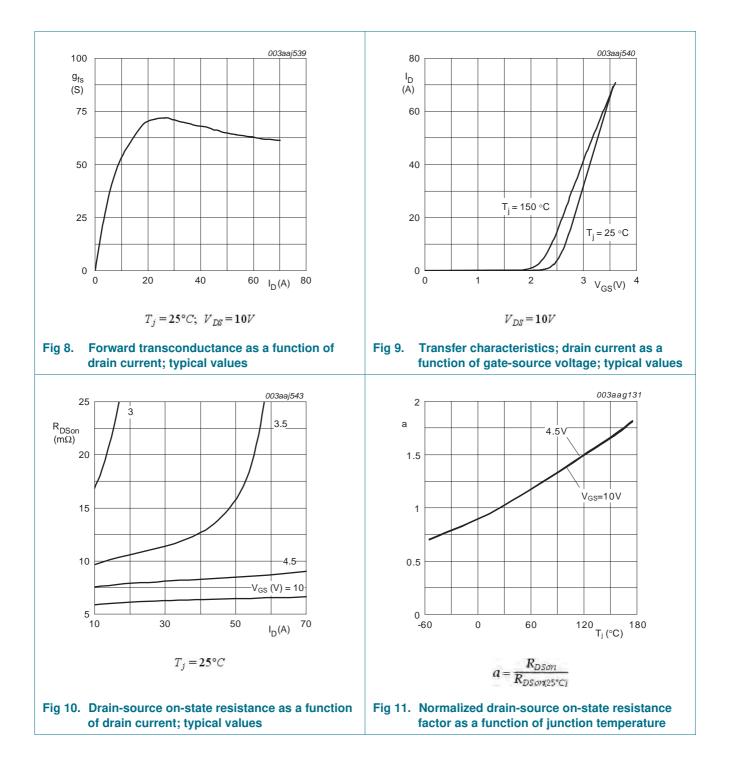
| Table 6. | Characteristics | | | | | |
|-----------------------------------|--|---|------|------|------|------|
| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
| Static cha | racteristics | | | | | |
| V _{(BR)DSS} | drain-source | $I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^\circ C$ | 30 | - | - | V |
| | breakdown voltage | $I_D = 250 \ \mu\text{A}; \ V_{GS} = 0 \ V; \ T_j = -55 \ ^\circ\text{C}$ | 27 | - | - | V |
| V _{GS(th)} | gate-source threshold voltage | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$ | 1.45 | 1.75 | 2.15 | V |
| $\Delta V_{GS(th)} / \Delta^{-1}$ | T gate-source threshold voltage variation with temperature | | - | -3.9 | - | mV/K |
| I _{DSS} | drain leakage current | $V_{DS} = 30 \ V; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$ | - | - | 1 | μΑ |
| | | $V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 ^{\circ}\text{C}$ | - | - | 100 | μA |
| I _{GSS} | gate leakage current | V_{GS} = 16 V; V_{DS} = 0 V; T_j = 25 °C | - | - | 100 | nA |
| | | V_{GS} = -16 V; V_{DS} = 0 V; T_j = 25 °C | - | - | 100 | nA |
| R _{DSon} | drain-source on-state resistance | V _{GS} = 4.5 V; I _D = 15 A; T _j = 25 °C; see <u>Figure 10</u> | - | 7.8 | 9 | mΩ |
| | | V _{GS} = 4.5 V; I _D = 15 A; T _j = 150 °C; see <u>Figure 10</u> ; see <u>Figure 11</u> | - | - | 15.3 | mΩ |
| | | V _{GS} = 10 V; I _D = 15 A; T _j = 25 °C; see <u>Figure 10</u> | - | 6.05 | 7 | mΩ |
| | | V _{GS} = 10 V; I _D = 15 A; T _j = 150 °C; see <u>Figure 10</u> ; see <u>Figure 11</u> | - | - | 11.9 | mΩ |
| R _G | gate resistance | f = 1 MHz | 1 | 2 | 4 | Ω |
| Dynamic of | characteristics | | | | | |
| Q _{G(tot)} | total gate charge | $I_D = 15 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 10 \text{ V};$ see <u>Figure 12</u> ; see <u>Figure 13</u> | - | 17.9 | - | nC |
| | | $I_D = 15 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 4.5 \text{ V};$ see <u>Figure 12</u> ; see <u>Figure 13</u> | - | 8.2 | - | nC |
| | | $I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$ | - | 16.2 | - | nC |
| Q _{GS} | gate-source charge | $I_D = 15 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 4.5 \text{ V};$ | - | 2.9 | - | nC |
| Q _{GS(th)} | pre-threshold gate-source charge | see <u>Figure 12;</u> see <u>Figure 13</u> | - | 1.9 | - | nC |
| Q _{GS(th-pl)} | post-threshold gate-source charge | | - | 1 | - | nC |
| Q _{GD} | gate-drain charge | | - | 2 | - | nC |
| V _{GS(pl)} | gate-source plateau voltage | I _D = 15 A; V _{DS} = 15 V; see <u>Figure 12</u> ; see <u>Figure 13</u> | - | 2.72 | - | V |
| C _{iss} | input capacitance | $V_{DS} = 15 V; V_{GS} = 0 V; f = 1 MHz;$ | - | 1076 | - | pF |
| C _{oss} | output capacitance | $T_j = 25 \text{ °C}; \text{ see } Figure 14$ | - | 248 | - | pF |
| C _{rss} | reverse transfer capacitance | | - | 88 | - | pF |

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| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|---------------------|----------------------------|--|-----|------|-----|------|
| t _{d(on)} | turn-on delay time | $V_{DS} = 15 \text{ V}; \text{ R}_{L} = 1 \Omega; \text{ V}_{GS} = 4.5 \text{ V};$ | - | 9.7 | - | ns |
| t _r | rise time | $R_{G(ext)} = 5 \Omega$ | - | 15.4 | - | ns |
| t _{d(off)} | turn-off delay time | | - | 13.4 | - | ns |
| t _f | fall time | | - | 8.5 | - | ns |
| Q _{oss} | output charge | $\label{eq:VGS} \begin{array}{l} V_{GS} = 0 \ V; \ V_{DS} = 15 \ V; \ f = 1 \ MHz; \\ T_j = 25 \ ^\circ C \end{array}$ | - | 24.7 | - | nC |
| Source-dra | in diode | | | | | |
| V _{SD} | source-drain voltage | I _S = 15 A; V _{GS} = 0 V; T _j = 25 °C; see <u>Figure 15</u> | - | 0.85 | 1.1 | V |
| t _{rr} | reverse recovery time | $I_{S} = 15 \text{ A}; dI_{S}/dt = -100 \text{ A}/\mu s; V_{GS} = 0 \text{ V};$ | - | 18.3 | - | ns |
| Q _r | recovered charge | $V_{DS} = 15 V$ | - | 11.9 | - | nC |
| t _a | reverse recovery rise time | $\label{eq:VGS} \begin{array}{l} V_{GS} = 0 \ V; \ I_S = 15 \ A; \ dI_S / dt = -100 \ A / \mu s; \\ V_{DS} = 15 \ V; \ see \ \overline{Figure \ 16} \end{array}$ | - | 11.4 | - | ns |
| t _b | reverse recovery fall time | | - | 6.9 | - | ns |

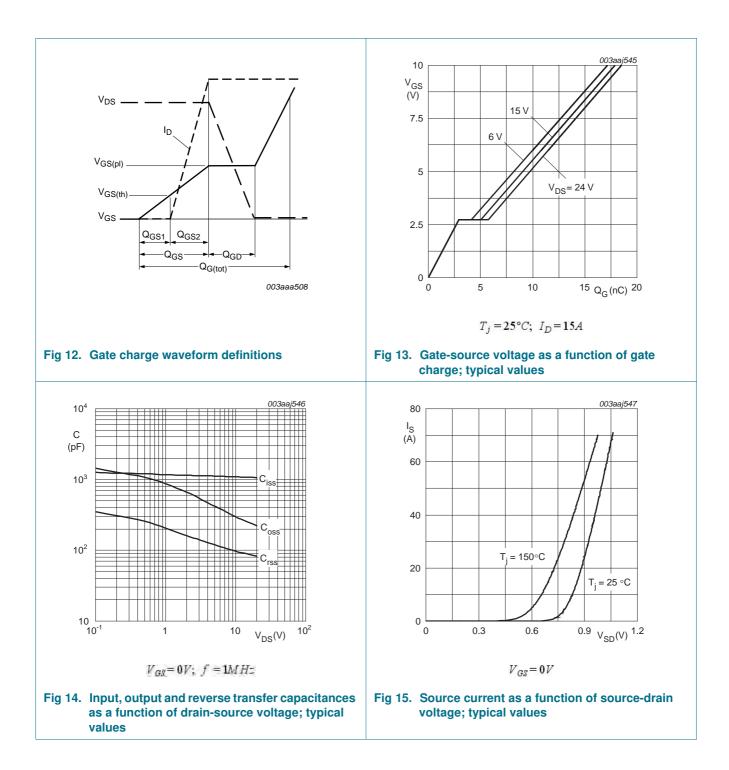


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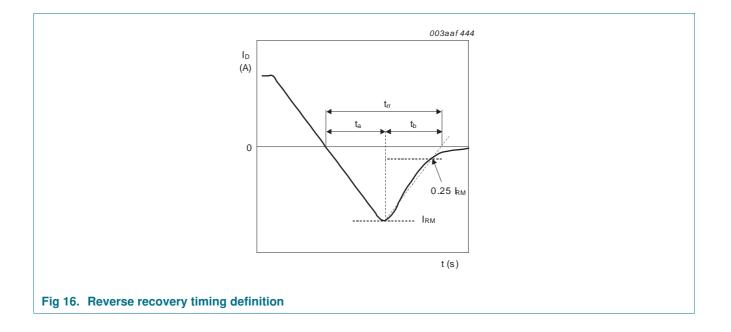


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7. Package outline

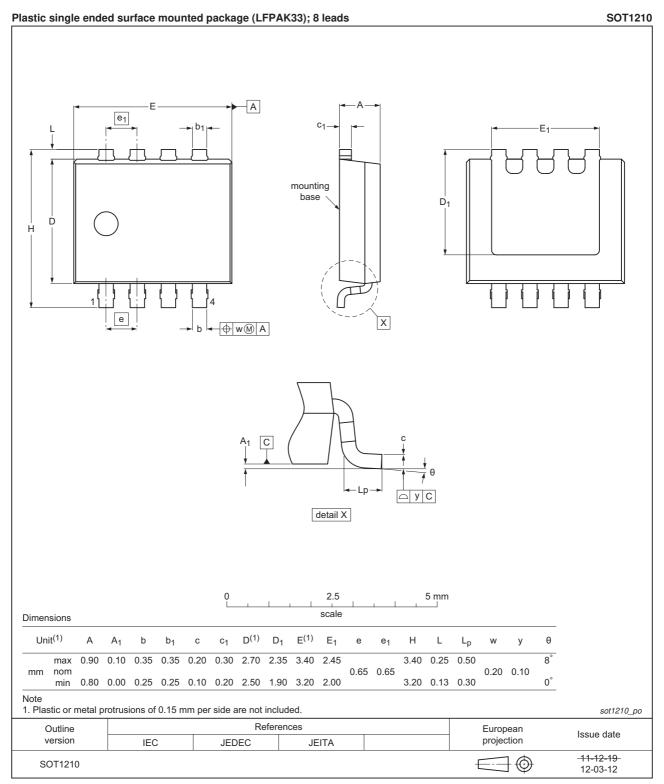


Fig 17. Package outline SOT1210 (LFPAK33)

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8. Revision history

Table 7.Revision history

| Document ID | Release date | Data sheet status | Change notice | Supersedes |
|-------------------|--|--|---------------|-------------------|
| PSMN7R0-30MLC v.4 | 20120615 | Product data sheet | - | PSMN7R0-30MLC v.3 |
| Modifications: | Status changed fromVarious changes to | om objective to product. o content. | | |
| PSMN7R0-30MLC v.3 | 20120607 | Objective data sheet | - | PSMN7R0-30MLC v.2 |

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|--------------------------------|-------------------------------|---|
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